

N-Channel 100 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY

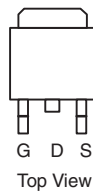
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
100	0.0095 at $V_{GS} = 10$ V	110 ^a

FEATURES

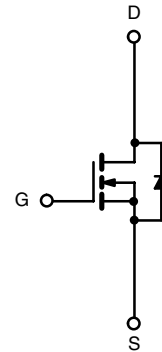
- TrenchFET[®] Power MOSFET
- New Package with Low Thermal Resistance
- 100 % R_g Tested


RoHS
COMPLIANT

TO-263



Ordering Information: SUM110N10-09-E3 (Lead (Pb)-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_C = 25$ °C, unless otherwise noted

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V_{DS}	100	V	
Gate-Source Voltage	V_{GS}	± 20		
Continuous Drain Current ($T_J = 175$ °C)	I_D	$T_C = 25$ °C	110 ^a	A
		$T_C = 125$ °C	87 ^a	
Pulsed Drain Current	I_{DM}	440		
Avalanche Current	I_{AR}	75		
Repetitive Avalanche Energy ^b	E_{AR}	L = 0.1 mH	280	mJ
Maximum Power Dissipation ^b		$T_C = 25$ °C	375 ^c	W
	$T_A = 25$ °C	3.75		
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Limit	Unit
Junction-to-Ambient	R_{thJA}	40	°C/W
Junction-to-Case (Drain)			

Notes:

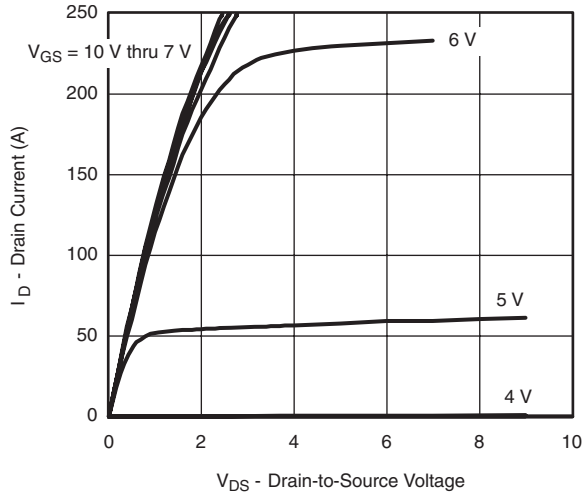
- Package limited.
- Duty cycle ≤ 1 %.
- See SOA curve for voltage derating.
- When mounted on 1" square PCB (FR-4 material).

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{DS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	100			V	
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2		4		
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}$			1	μA	
		$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$			50		
		$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^\circ\text{C}$			250		
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	120			A	
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 30\text{ A}$		0.0078	0.0095	Ω	
		$V_{GS} = 10\text{ V}, I_D = 30\text{ A}, T_J = 125\text{ }^\circ\text{C}$			0.017		
		$V_{GS} = 10\text{ V}, I_D = 30\text{ A}, T_J = 175\text{ }^\circ\text{C}$			0.025		
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 30\text{ A}$	25			S	
Dynamic^b							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		6700		μF	
Output Capacitance	C_{oss}			750			
Reverse Transfer Capacitance	C_{rss}			280			
Total Gate Charge ^c	Q_g	$V_{DS} = 50\text{ V}, V_{GS} = 10\text{ V}, I_D = 85\text{ A}$		110	160	nC	
Gate-Source Charge ^c	Q_{gs}			24			
Gate-Drain Charge ^c	Q_{gd}			24			
Gate Resistance	R_g		1.0		6.2	Ω	
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = 50\text{ V}, R_L = 0.6\text{ }\Omega$ $I_D \cong 85\text{ A}, V_{GEN} = 10\text{ V}, R_g = 2.5\text{ }\Omega$		20	30	ns	
Rise Time ^c	t_r			125	200		
Turn-Off Delay Time ^c	$t_{d(off)}$			55	85		
Fall Time ^c	t_f			130	195		
Source-Drain Diode Ratings and Characteristics $T_C = 25\text{ }^\circ\text{C}^b$							
Continuous Current	I_S				110	A	
Pulsed Current	I_{SM}				240		
Forward Voltage ^a	V_{SD}	$I_F = 85\text{ A}, V_{GS} = 0\text{ V}$		1.0	1.5	V	
Reverse Recovery Time	t_{rr}	$I_F = 50\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		70	140	ns	
Peak Reverse Recovery Charge	$I_{RM(REC)}$				5.5	10	A
Reverse Recovery Charge	Q_{rr}				0.19	0.35	μC

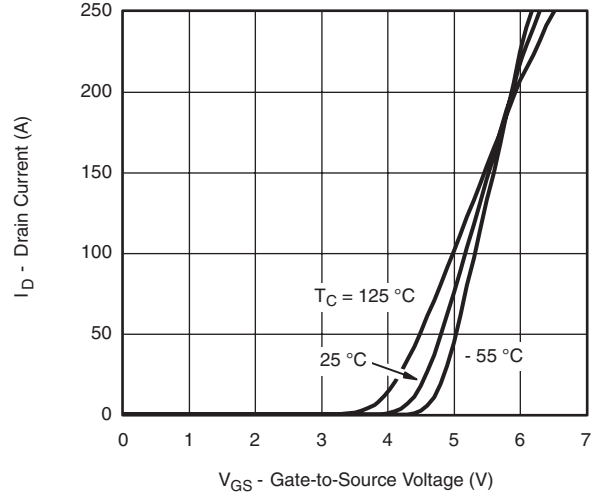
Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

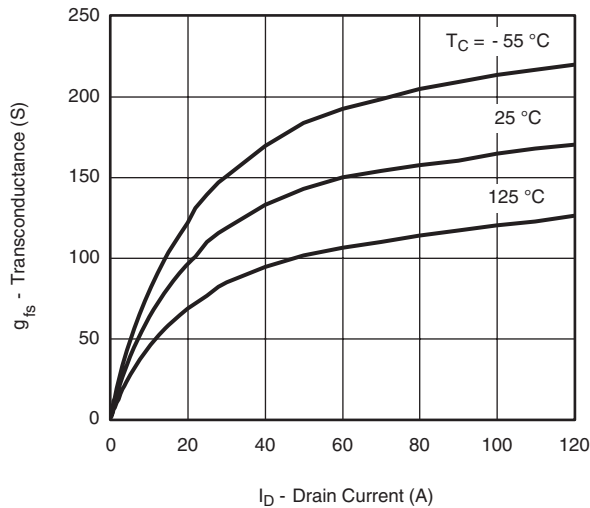
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


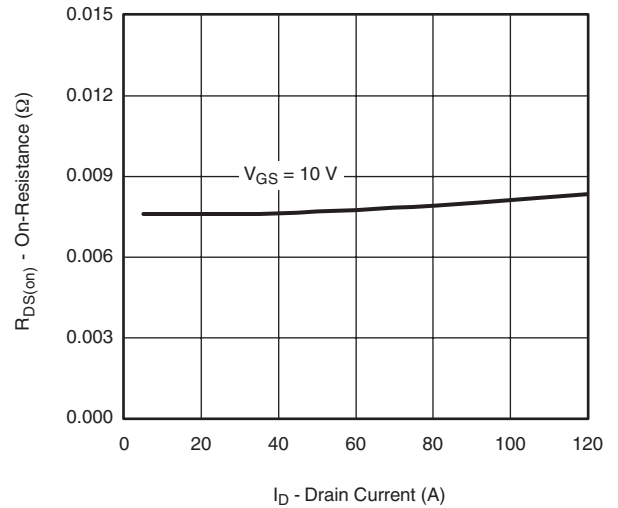
$V_{GS} = 10\text{ V thru } 7\text{ V}$
Output Characteristics



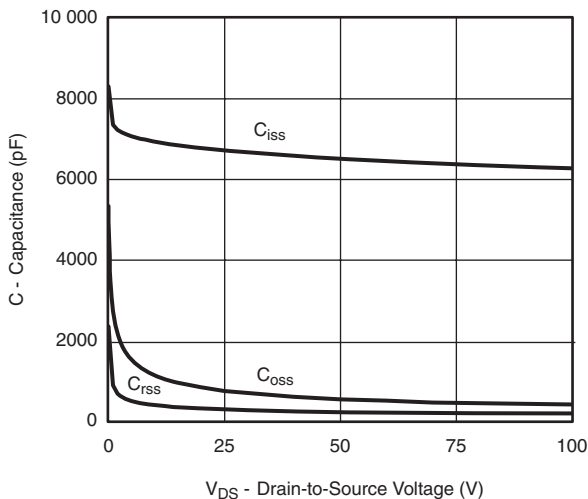
$T_C = 125^\circ\text{C}$
 25°C
 -55°C
Transfer Characteristics



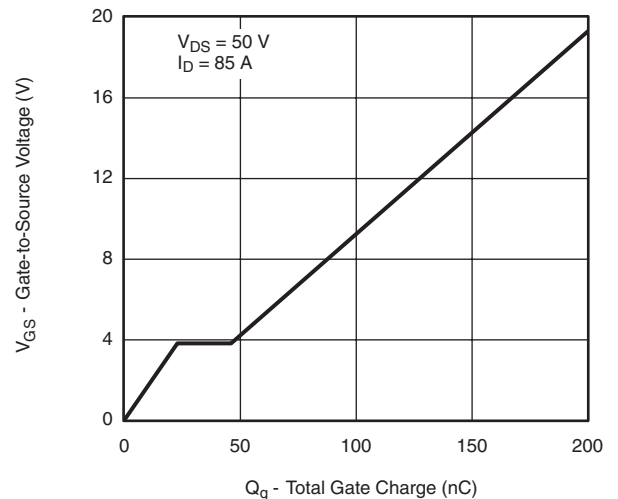
$T_C = -55^\circ\text{C}$
 25°C
 125°C
Transconductance



$V_{GS} = 10\text{ V}$
On-Resistance vs. Drain Current

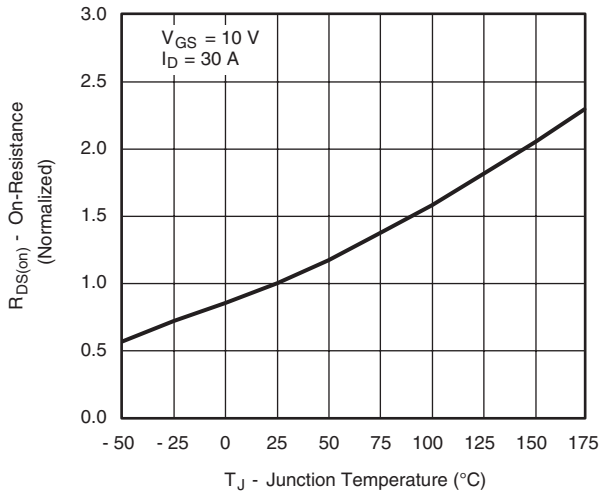


C_{iss}
 C_{oss}
 C_{rss}
Capacitance

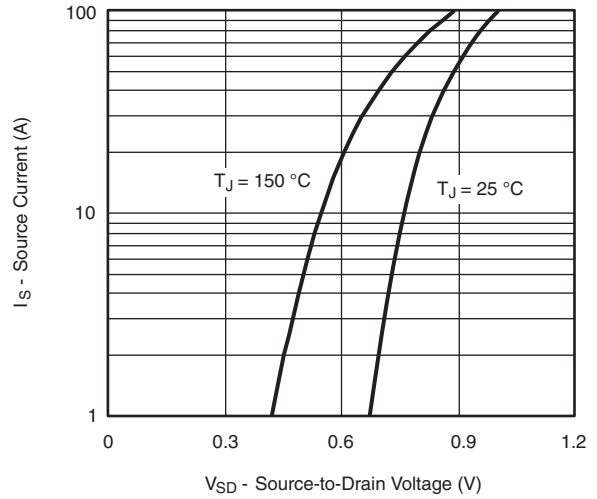


$V_{DS} = 50\text{ V}$
 $I_D = 85\text{ A}$
Gate Charge

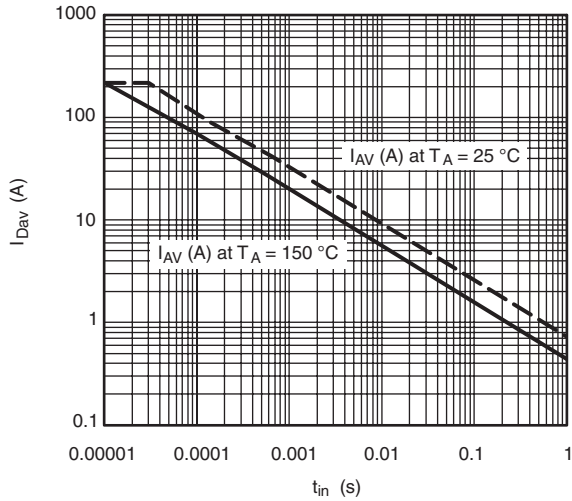
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



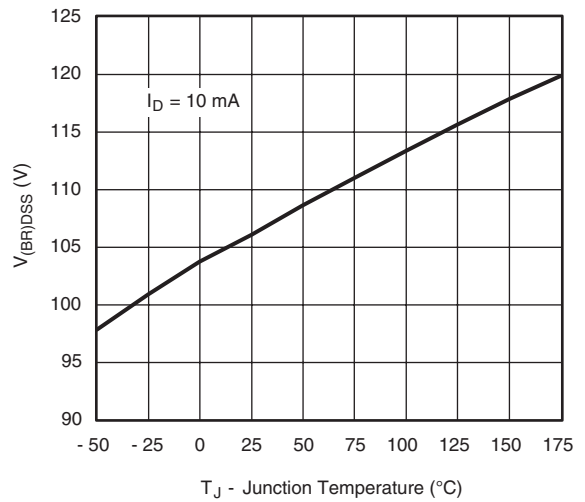
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

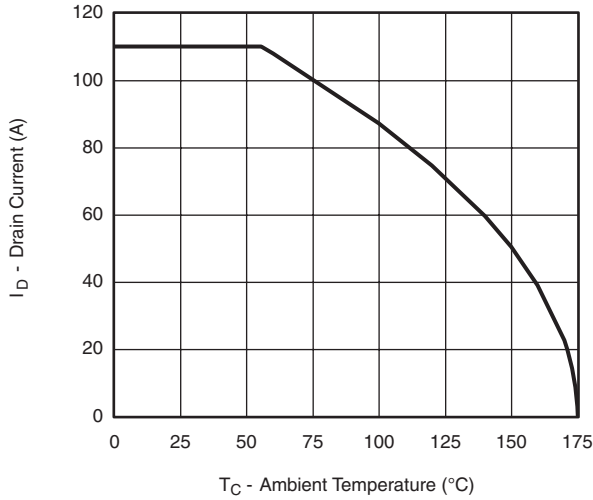


Avalanche Current vs. Time

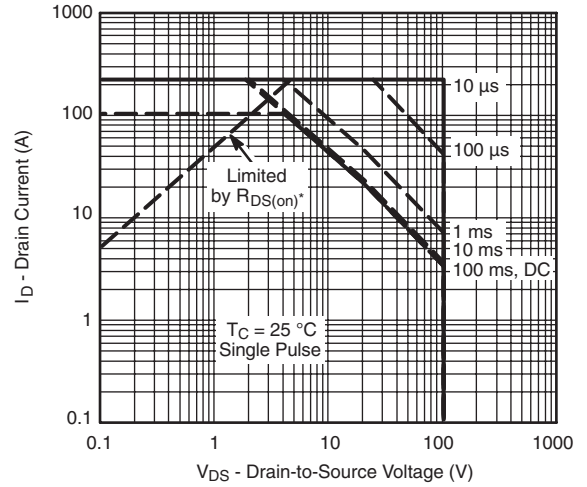


Drain Source Breakdown vs. Junction Temperature

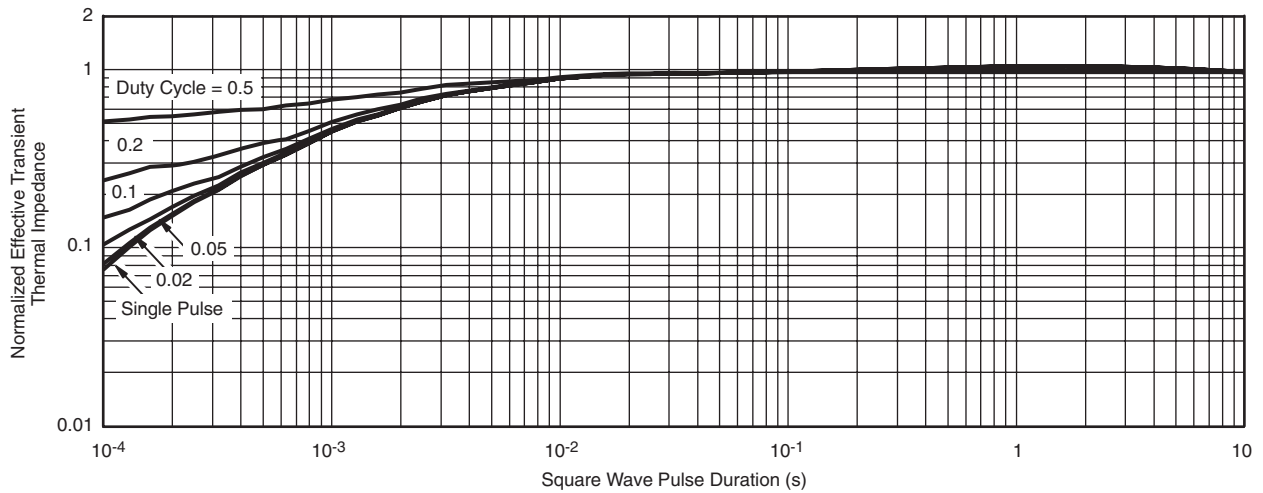
THERMAL RATINGS



Maximum Avalanche and Drain Current vs. Case Temperature



Safe Operating Area
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?70677.

TO-263 (D²PAK): 3-LEAD



DIM.	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	0.160	0.190	4.064	4.826	
b	0.020	0.039	0.508	0.990	
b1	0.020	0.035	0.508	0.889	
b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457
	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
	Thick lead	0.023	0.027	0.584	0.685
c2	0.045	0.055	1.143	1.397	
D	0.340	0.380	8.636	9.652	
D1	0.220	0.240	5.588	6.096	
D2	0.038	0.042	0.965	1.067	
D3	0.045	0.055	1.143	1.397	
D4	0.044	0.052	1.118	1.321	
E	0.380	0.410	9.652	10.414	
E1	0.245	-	6.223	-	
E2	0.355	0.375	9.017	9.525	
E3	0.072	0.078	1.829	1.981	
e	0.100 BSC		2.54 BSC		
K	0.045	0.055	1.143	1.397	
L	0.575	0.625	14.605	15.875	
L1	0.090	0.110	2.286	2.794	
L2	0.040	0.055	1.016	1.397	
L3	0.050	0.070	1.270	1.778	
L4	0.010 BSC		0.254 BSC		
M	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13					
DWG: 5843					

Notes

- Plane B includes maximum features of heat sink tab and plastic.
- No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- Pin-to-pin coplanarity max. 4 mils.
- *: Thin lead is for SUB, SYB.
Thick lead is for SUM, SYM, SQM.
- Use inches as the primary measurement.
- This feature is for thick lead.

RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

[Return to Index](#)



Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Vishay products are not designed for use in life-saving or life-sustaining applications or any application in which the failure of the Vishay product could result in personal injury or death unless specifically qualified in writing by Vishay. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.